



Infrared Emitting Diode

Detailed product specifications are available on: us.100y.com.tw



The EL-1K3 is a high-power GaAs IRED mounted in durable, hermetically sealed TO-18 metal can package, which provides years of reliable performance even under demanding conditions such as use outdoors.

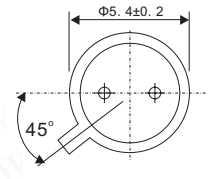
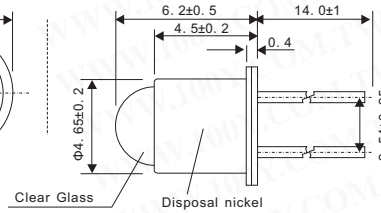
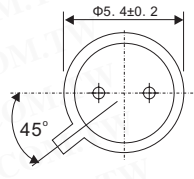
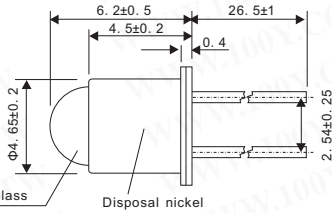
FEATURES

- Wide beam angel
- Durable
- High reliability in demanding environments

APPLICATIONS

- Optical emitters
- Optical switches
- Smoke sensors

Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	Vf@If(mA)	λP(nm)	Δθ(deg)	If max.	Vr max.
18112	EL-1K3	KODENSHI	Infrared Emitting Diode	TO-18	200mW	1.35V/100mA	940	±36	100	5V



The EL-1KL3 and 1KL5 are high-power GaAs IREDs mounted in durable, hermetically sealed TO-18 metal can package, which provides years of reliable performance even under demanding conditions such as use outdoors.

FEATURES

- Narrow beam angle
- Durable
- High reliability in demanding environments

APPLICATIONS

- Optical emitters
- Optical switches
- Emcoders
- Smoke sensors

Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	Vf@If(mA)	λP(nm)	Δθ(deg)	If max.	Vr max.
3773	EL-1KL3	KODENSHI	Infrared Emitting Diode	TO-18	170	1.7V/100mA	940	±8	100	5v



Infrared Emitting Diode

Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	Vf@If(mA)	λP(nm)	Δθ(deg)	If max.	Vr max.
3851	EL-1L7 (D)	OPTOSENSOR	Infrared Emitting Diode	Epoxy resin	100	1.7V/100mA	940	±30	100	5v



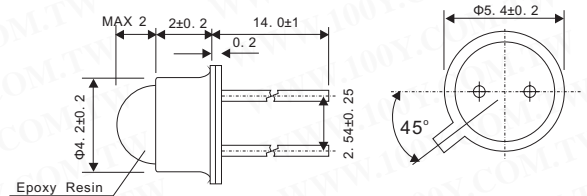
The EL-1ML2, a high-power GaAs IRED mounted in a TO-18 type header with clear epoxy encapsulation, has wide beam angle and is relatively low-cost compared to TO-18 can-type devices.

FEATURES

- Wide beam angle
- Relative low cost against metal can package
- Low profile package

APPLICATIONS

- Optical switches
- Encoders
- Optical readers

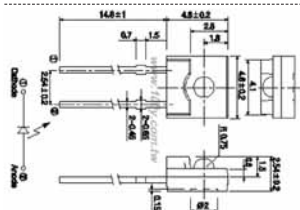


Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	Vf@If(mA)	λP(nm)	Δθ(deg)	If max.	Vr max.
18158	EL-1ML2	KODENSHI	Infrared Emitting Diode	TO-18	170	1.2V/50mA	940	±32	100	5V



Infrared Emitting Diode

Part No.	Product No.	Manufacturer	Description	Po (mW)	Vf@If(mA)
43452	EL-8L	KODENSHI	Infrared Emitting Diode	80	1.2V/60mA



Infrared Emitting Diodes(GaAs)

Part No.	Product No.	Manufacturer	Description	Package	Po (mW)	λP(nm)	Δθ(deg)	If max.	Vr max.
33081	EL23G	KODENSHI	Infrared Emitting Diodes(GaAs)	Sidelooking plastic package	100 mW	940nm	±30 deg	60mA	5V

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